DATA SHEET

NEC

MOS FIELD EFFECT TRANSISTOR

μPA1757

SWITCHING
N-CHANNEL POWER MOS FET
INDUSTRIAL USE

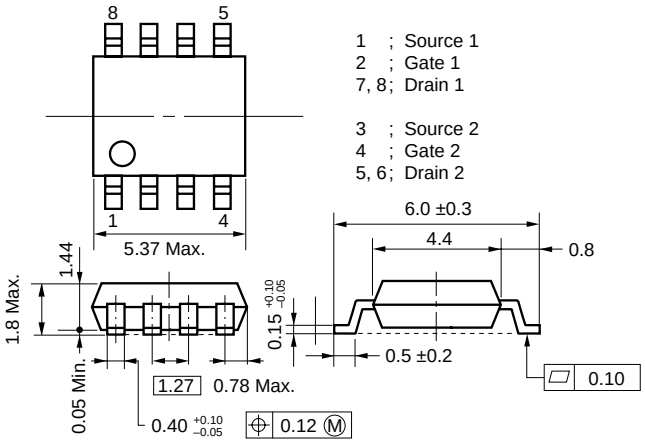
Description

This product is Dual N-Channel MOS Field Effect Transistor designed for power management application of notebook computers, and Li-ion battery application.

Features

- Dual MOS FET chips in small package
- 2.5 V gate drive type and low on-resistance
  $R_{DS(on)1}$ = 23 mΩ (MAX.) (V_{GS} = 4.5 V, I_D = 3.5 A)
  $R_{DS(on)2}$ = 32 mΩ (MAX.) (V_{GS} = 2.5 V, I_D = 3.5 A)
- Low C_{iss} C_{iss} = 750 pF Typ.
- Built-in G-S protection diode
- Small and surface mount package (Power SOP8)

Package Drawing (Unit : mm)

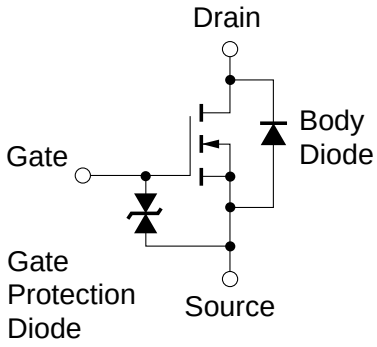


Ordering information

Part Number	Package
μPA1757G	Power SOP8

Absolute Maximum Ratings (T_A = 25 °C)

Drain to source voltage	V_{DSS}	20	V
Gate to source voltage	V_{GSS}	±12.0	V
Drain current (DC)	$I_{D(DC)}$	±7.0	A
Drain current (pulse)[Note1]	$I_{D(pulse)}$	±28	A
Total power dissipation (1 unit)[Note2]	P_T	1.7	W
Total power dissipation (2 unit)[Note2]	P_T	2.0	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	–55 to +150	°C



Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1 %

2. T_A = 25 °C, Mounted on ceramic substrate of 2000 mm^2 x 1.1 mm

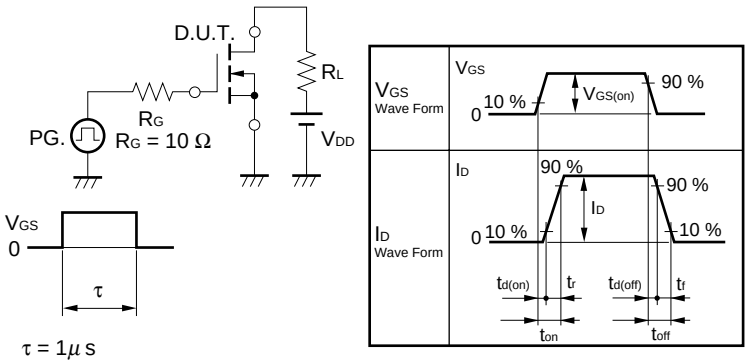
The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Document No. D12910EJ2V0DS00 (2nd edition)
Date Published September 1998 NS CP (K)
Printed in Japan

Electrical Characteristics (T_A = 25 °C)

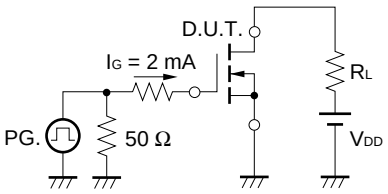
Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to source on-state resistance	$R_{DS(on)1}$	V_{GS} = 4.5 V, I_D = 3.5 A		16.2	23	mΩ
	$R_{DS(on)2}$	V_{GS} = 2.5 V, I_D = 3.5 A		22	32	mΩ
Gate to source cutoff voltage	$V_{GS(off)}$	V_{DS} = 10 V, I_D = 1.0 mA	0.5	0.8	1.5	V
Forward transfer admittance	$\|y_{fs}\|$	V_{DS} = 10 V, I_D = 3.5 A	5.0	13		S
Drain leakage current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			10	μA
Gate to source leakage current	I_{GSS}	V_{GS} = ±12.0 V, V_{DS} = 0 V			±10	μA
Input capacitance	C_{iss}	V_{DS} = 10 V V_{GS} = 0 V f = 1 MHz		750		pF
Output capacitance	C_{oss}			420		pF
Reverse transfer capacitance	C_{rss}			140		pF
Turn-on delay time	$t_{d(on)}$	I_D = 3.5 A $V_{GS(on)}$ = 4.0 V V_{DD} = 10 V R_G = 10 Ω		57		ns
Rise time	t_r			206		ns
Turn-off delay time	$t_{d(off)}$			593		ns
Fall time	t_f			815		ns
Total gate charge	Q_G	I_D = 7.0 A V_{DD} = 16 V V_{GS} = 4.0 V		13.0		nC
Gate to source charge	Q_{GS}			2.6		nC
Gate to drain charge	Q_{GD}			5.3		nC
Body diode forward voltage	$V_{F(S-D)}$	I_F = 7.0 A, V_{GS} = 0 V		0.75		V

Test circuit 1 Switching time



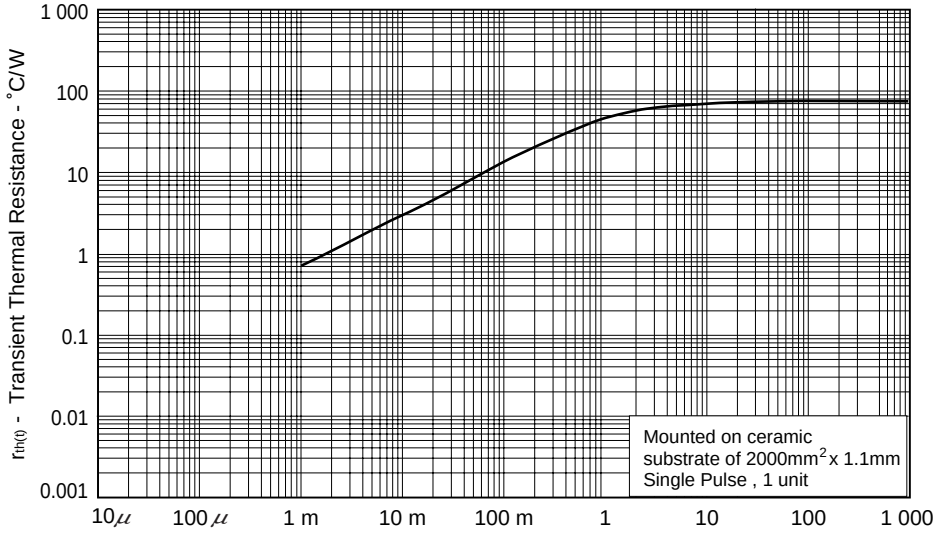
τ = 1μs
Duty Cycle ≤ 1 %

Test circuit 2 Gate charge

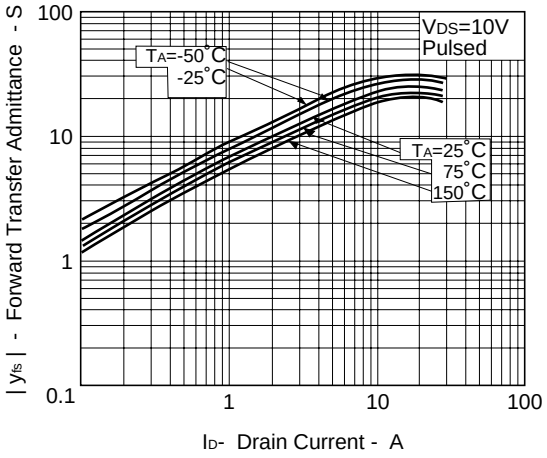


Typical Characteristics (T_A = 25 °C)

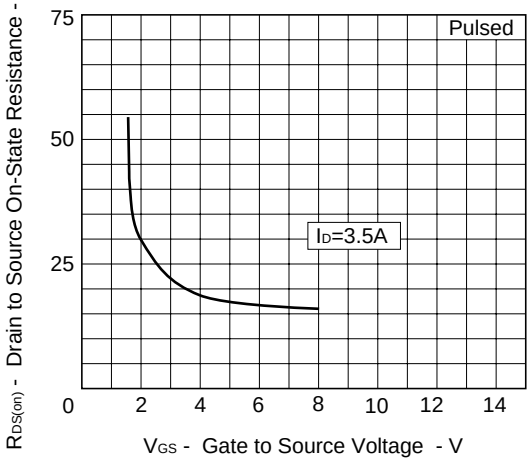
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



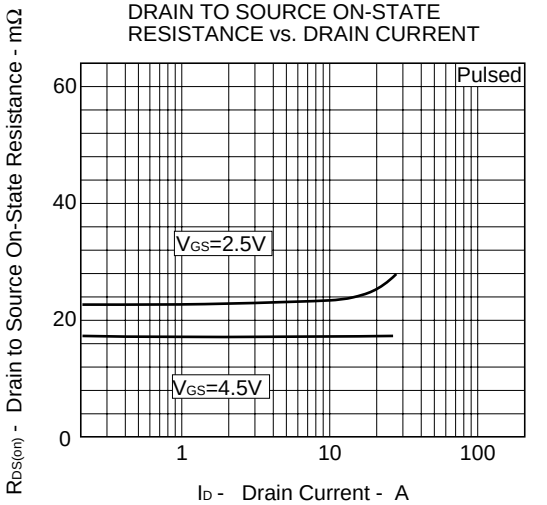
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



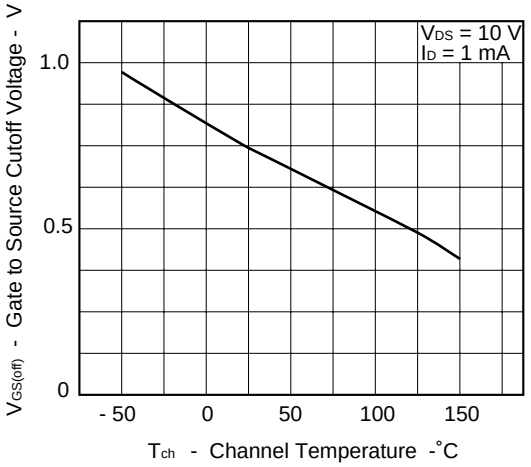
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



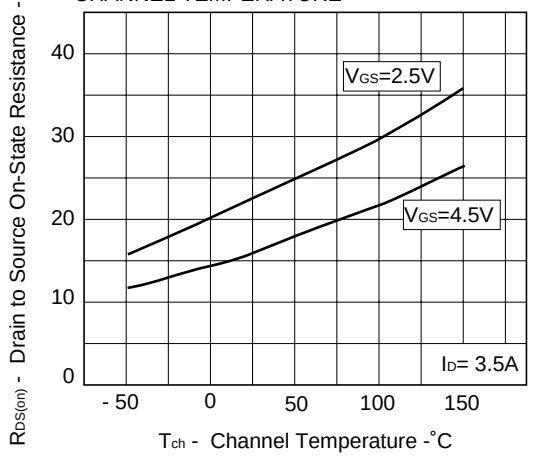
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



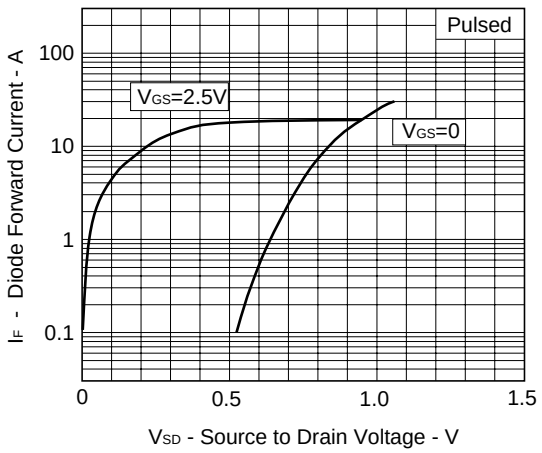
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



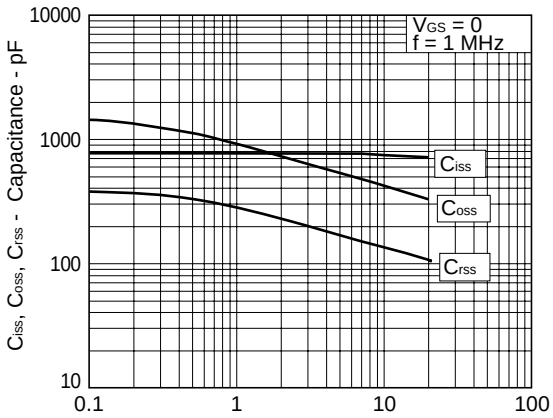
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



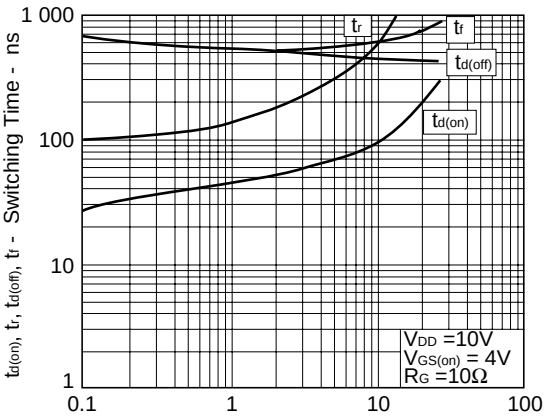
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



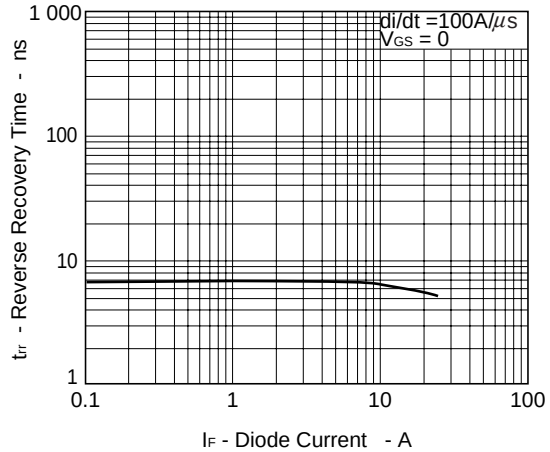
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



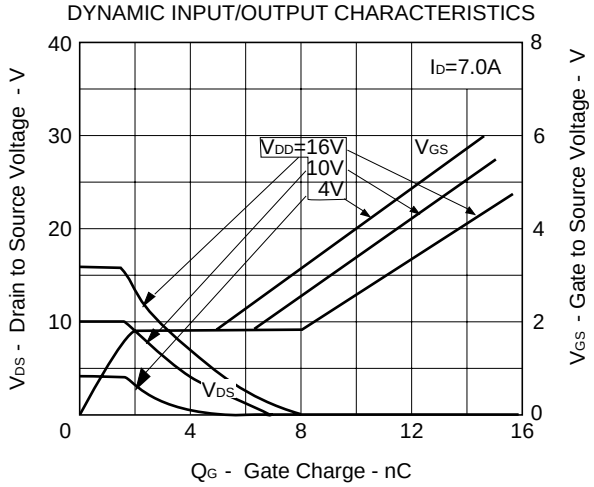
SWITCHING CHARACTERISTICS



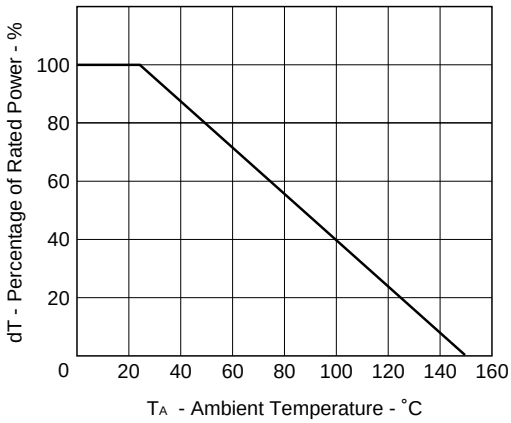
REVERSE RECOVERY TIME vs. DRAIN CURRENT



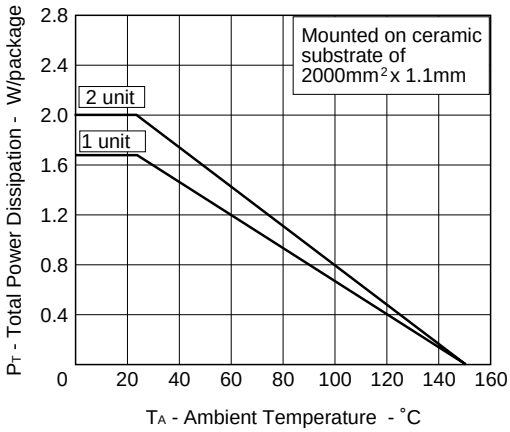
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



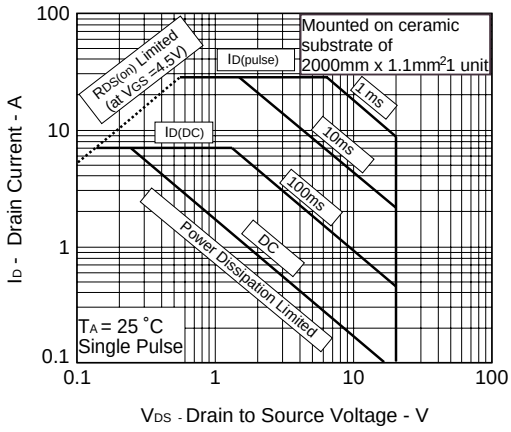
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



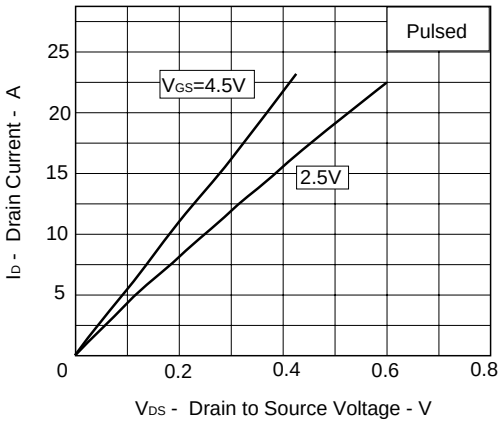
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



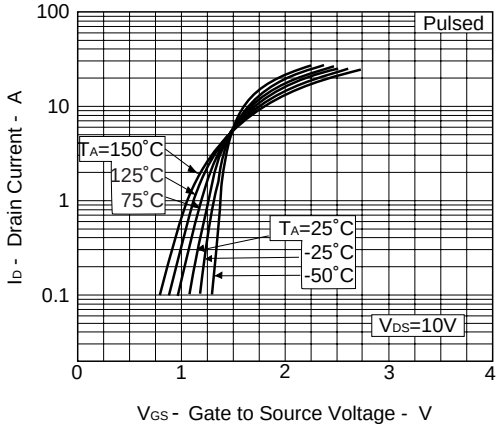
FORWARD BIAS SAFE OPERATING AREA



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



FORWARD TRANSFER CHARACTERISTICS



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